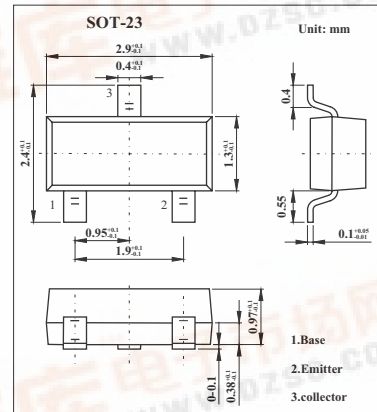


SMD Type Transistors

Silicon PNP Epitaxial  
2SA1171

■ Features

- Low frequency small signal amplifier



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V <sub>CB0</sub>	-90	V
Collector to emitter voltage	V <sub>CEO</sub>	-90	V
Emitter to base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>c</sub>	-50	mA
Collector power dissipation	P <sub>c</sub>	150	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = -1 mA, R <sub>BE</sub> = ∞	-90			V
Collector cutoff current	I <sub>cBO</sub>	V <sub>CB</sub> = -75 V, I <sub>E</sub> = 0			-0.5	μA
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = -12 V, I <sub>c</sub> = -2 mA	250		800	
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -12 V, I <sub>c</sub> = -2 mA			-0.75	V
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = -10 mA, I <sub>b</sub> = -1 mA			-0.5	V
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = -12 V, I <sub>c</sub> = -2 mA		200		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -25 V, I <sub>E</sub> = 0, f = 1 MHz		1.6		pF

■ hFE Classification

Marking	PD	PE
hFE	250~500	400~800

